

REDUCING PARASITIC CONDUCTIVE
PATHS IN PHASE CHANGE MEMORIES

Abstract of the Disclosure

A phase change memory may be formed by defining a pore in an insulator over a semiconductor substrate. The pore may be filled with a metallic material to form a high
5 resistance heater. A portion of the metallic material may be removed at the upper end of the pore. Thereafter, when the phase change material is deposited, a portion of the phase change material fills the upper end of the pore and the remainder of the phase change material overlies the
10 pore and the insulator. A conductive material may be formed atop the phase change material. As a result, the creation of a parasitic path from a corner of the metallic heater to the overlying conductive material may be less likely.